

# NRV TSA4100E

## Trench-Based Schottky Rectifier, Low Leakage

### Features

- Fine Lithography Trench-based Schottky Technology for Very Low Forward Voltage and Low Leakage
- Fast Switching with Exceptional Temperature Stability
- Low Power Loss and Lower Operating Temperature
- Higher Efficiency for Achieving Regulatory Compliance
- High Surge Capability
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

### Typical Applications

- Switching Power Supplies including Wireless, Smartphone and Notebook Adapters
- High Frequency and DC-DC Converters
- Freewheeling and OR-ing diodes
- Reverse Battery Protection
- Instrumentation
- LED Lighting

### Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets Flammability Rating UL 94-0 @ 0.125 in.
- Lead Finish: 100% Matte Sn (Tin)
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Device Meets MSL 1 Requirements



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**SCHOTTKY BARRIER  
RECTIFIERS  
4 AMPERES  
100 VOLTS**

### MARKING DIAGRAMS



**SMA  
CASE 403D  
STYLE 1**



TE41 = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

### ORDERING INFORMATION

Device	Package	Shipping†
NRV TSA4100ET3G	SMA (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

# NRVTSA4100E

## MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	100	V
Average Rectified Forward Current ( $T_L = 142^\circ\text{C}$ )	$I_{F(AV)}$	4.0	A
Peak Repetitive Forward Current, (Square Wave, 20 kHz, $T_L = 135^\circ\text{C}$ )	$I_{FRM}$	8.0	A
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	$I_{FSM}$	150	A
Storage Temperature Range	$T_{stg}$	-65 to +175	$^\circ\text{C}$
Operating Junction Temperature	$T_J$	-55 to +175	$^\circ\text{C}$
ESD Rating (Human Body Model)		1B	
ESD Rating (Machine Model)		M3	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Typ	Max	Unit
Thermal Resistance, Junction-to-Lead, Steady State (Assumes 600 mm <sup>2</sup> 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JL}$	–	16.2	$^\circ\text{C/W}$
Thermal Resistance, Junction-to-Ambient, Steady State (Assumes 600 mm <sup>2</sup> 1 oz. copper bond pad, on a FR4 board)	$R_{\theta JA}$	–	90	$^\circ\text{C/W}$

## ELECTRICAL CHARACTERISTICS

Instantaneous Forward Voltage (Note 1) ( $i_F = 1.0$ Amps, $T_J = 25^\circ\text{C}$ ) ( $i_F = 4.0$ Amps, $T_J = 25^\circ\text{C}$ )  ( $i_F = 1.0$ Amps, $T_J = 125^\circ\text{C}$ ) ( $i_F = 4.0$ Amps, $T_J = 125^\circ\text{C}$ )	$V_F$	0.45 0.61  0.36 0.53	– 0.68  – 0.59	V
Reverse Current (Note 1) (Rated dc Voltage, $T_J = 25^\circ\text{C}$ ) (Rated dc Voltage, $T_J = 125^\circ\text{C}$ )	$i_R$	3.5 2.0	29 5.0	$\mu\text{A}$ mA
Diode Capacitance (Rated dc Voltage, $T_J = 25^\circ\text{C}$ , $f = 1$ MHz)	$C_d$	55		pF

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300  $\mu\text{s}$ , Duty Cycle  $\leq 2.0\%$ .

TYPICAL CHARACTERISTICS

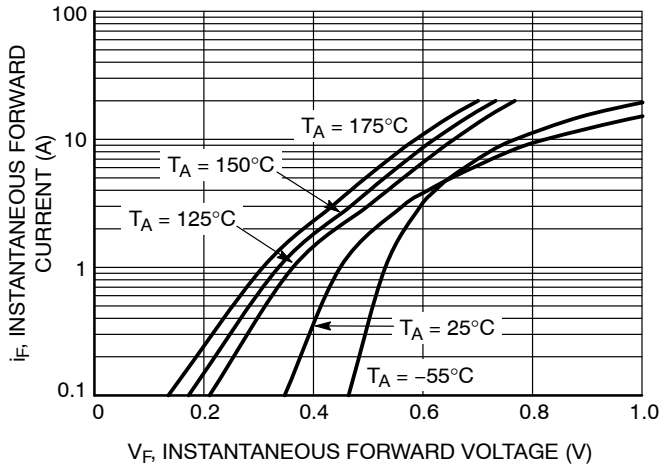


Figure 1. Typical Instantaneous Forward Characteristics

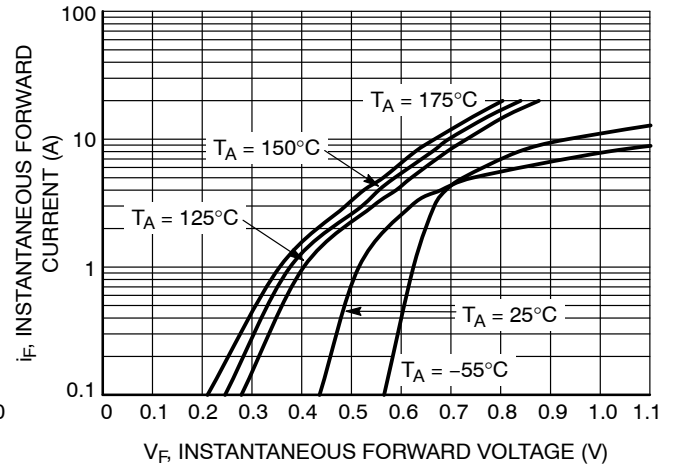


Figure 2. Maximum Instantaneous Forward Characteristics

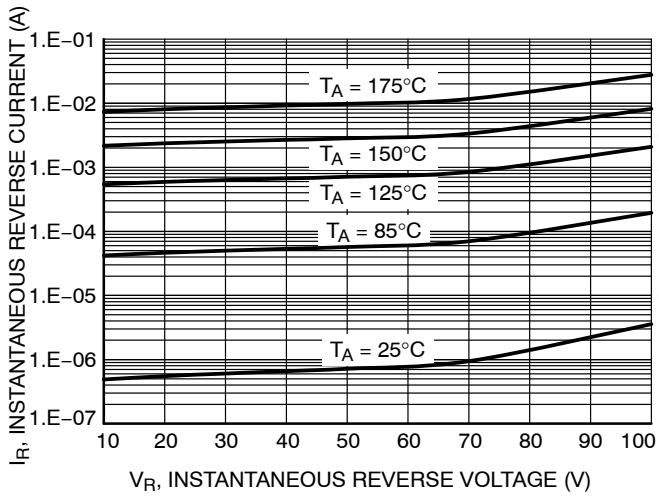


Figure 3. Typical Reverse Characteristics

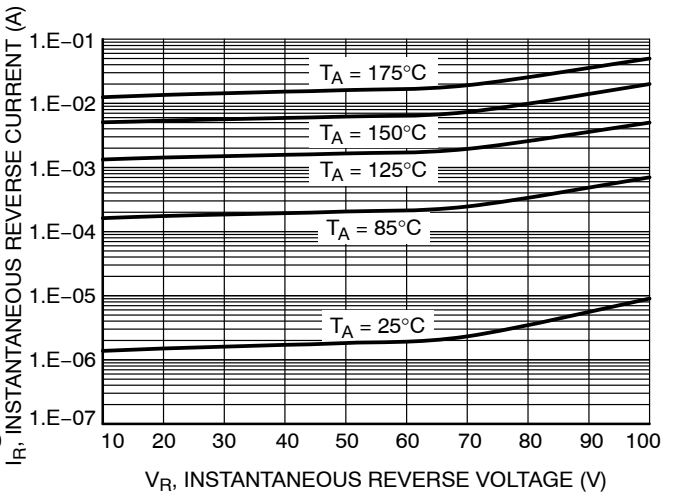


Figure 4. Maximum Reverse Characteristics

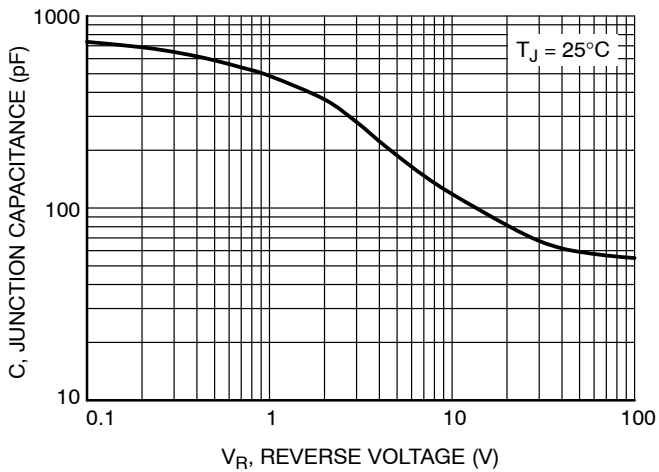


Figure 5. Typical Junction Capacitance

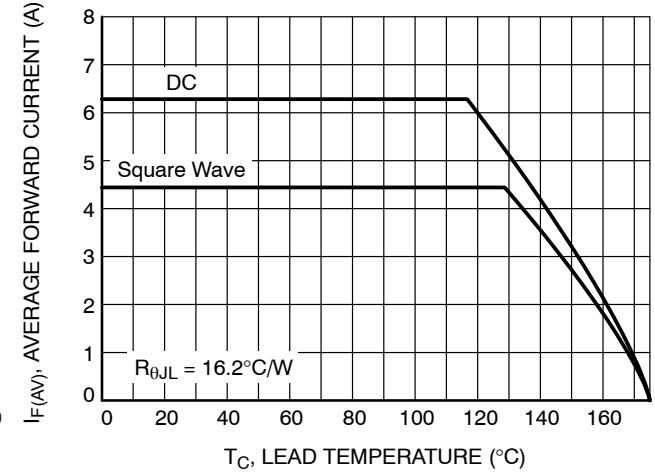


Figure 6. Current Derating

TYPICAL CHARACTERISTICS

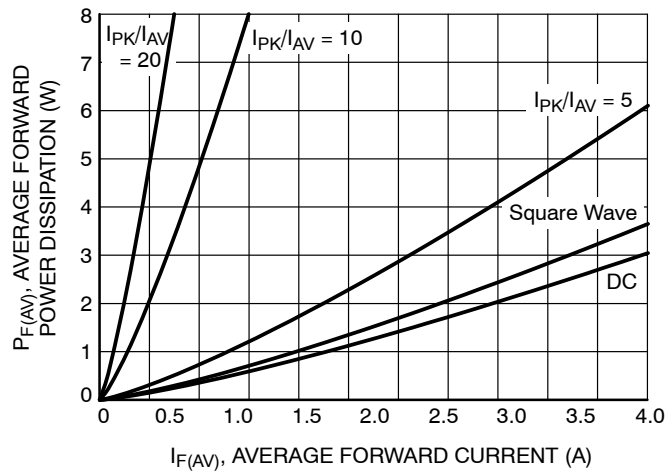


Figure 7. Forward Power Dissipation

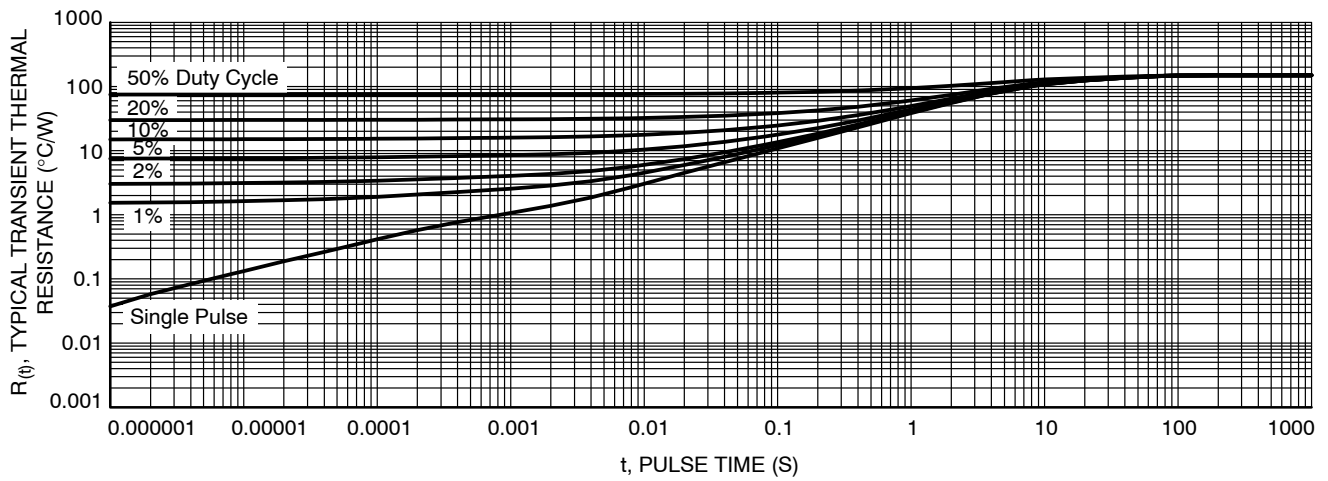


Figure 8. Typical Transient Thermal Response, Junction-to-Ambient

# MECHANICAL CASE OUTLINE

## PACKAGE DIMENSIONS

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STYLE 1

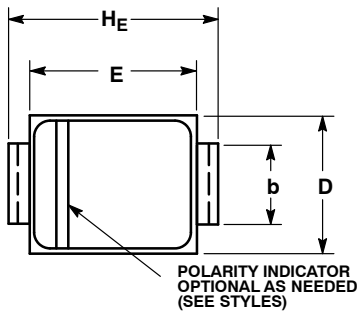


STYLE 2

SCALE 1:1

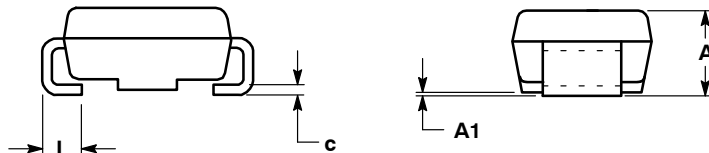
### SMA CASE 403D ISSUE H

DATE 23 SEP 2015

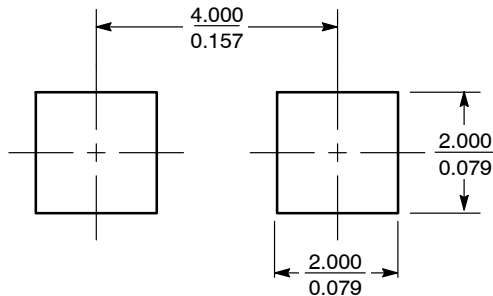


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. DIMENSION b SHALL BE MEASURED WITHIN DIMENSION L.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.97	2.10	2.20	0.078	0.083	0.087
A1	0.05	0.10	0.20	0.002	0.004	0.008
b	1.27	1.45	1.63	0.050	0.057	0.064
c	0.15	0.28	0.41	0.006	0.011	0.016
D	2.29	2.60	2.92	0.090	0.103	0.115
E	4.06	4.32	4.57	0.160	0.170	0.180
HE	4.83	5.21	5.59	0.190	0.205	0.220
L	0.76	1.14	1.52	0.030	0.045	0.060



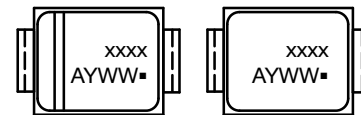
### SOLDERING FOOTPRINT\*



SCALE 8:1 (mm/inches)

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

### GENERIC MARKING DIAGRAM\*



STYLE 1

STYLE 2

xxxx = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
▪ = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLE 1:  
PIN 1. CATHODE (POLARITY BAND)  
2. ANODE

STYLE 2:  
NO POLARITY

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